Crownpo Technology

5-Line ESD Protection Array

DESCRIPTION

- The ESDV65V0U are designed by TVS array that is to protect sensitive electronics from damage or latchup due to ESD.
- ◆ They are designed for use in applications where board space is at a premium.
- ◆ ESDV65V0U will protect up to five lines, and may be used on lines where the signal polarities swing above and below ground.
- ◆ ESDV65V0U offer desirable characteristics for board level protection including fast response time, low operating and clamping voltage, and no device degradation.
- ◆ ESDV65V0U may be used to meet the immunity requirements of IEC 61000-4-2, level 4.
- The small SOT-363 package makes them ideal for use in portable electronics such as cell phones, PDA's, notebook computers, and digital cameras.

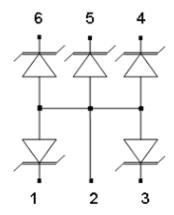
FEATURES

- ◆ Transient protection for data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns)
- Protects five I/O lines
- Working voltage : 5V
- ◆ Low leakage current
- Low operating and clamping voltages

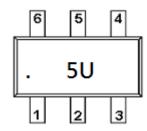
APPLICATIONS

- Cellular Handsets and Accessories
- Cordless Phone
- ◆ PDA
- Notebooks and Handhelds
- ♦ Portable Instrumentation
- Digital Cameras
- MP3 Player

PIN CONFIGURATION (SOT-363)



PART MARKING





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5-Line ESD Protection Array

ORDERING INFORMATION

Part Number	Package	Packing	Marking
ESDV65V0U	SOT-363	3K/7" Reel	5U

ABSOULTE MAXIMUM RATINGS

(Ta=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Peak Pulse Power (tp = 8/20 μs)	Ppk	100	W
Maximum Peak Pulse Current ($tp = 8/20 \mu s$)	Ipp	8	A
ESD per IEC 61000 – 4 – 2 (Air)	Vpp	±15	KV
ESD per IEC 61000 – 4 – 2 (Contact)	Vpp	±8	KV
Operating Junction Temperature	Тл	-55 ~ 125	$^{\circ}\!\mathbb{C}$
Storage Temperature Range	Tstg	-55 ~ 150	$^{\circ}\!\mathbb{C}$
Lead Soldering Temperature	TL	260 (10sec)	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS

(TA=25°C unless otherwise noted)

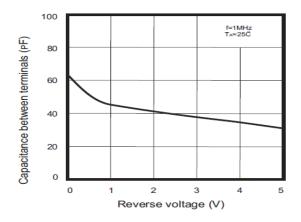
Parameter	Symbol	Conditions	Min.	Тур	Max.	Unit
Reverse Stand – Off Voltage	Vrwm				5	V
Reverse Breakdown Voltage	VBR	It = 1mA	6		7.6	V
Reverse Leakage Current	IR	$V_{RWM} = 5V$, $T=25^{\circ}C$			1	μΑ
Forward Voltage	VF	I _F =10mA			1.0	V
Clamping Voltage	Vc	Ipp =8A, tp = $8/20 \mu s$			13	V
Junction Capacitance	Cj	Between I/O Pin and GND VR = 0V, f = 1MHz			60	pF





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TYPICAL CHARACTERISTICS



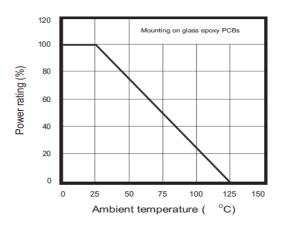


Fig 1: Junction Capacitance V.S Reverse Voltage Applied

Fig 2: Peak Plus Power V.S Exponential Plus Duration

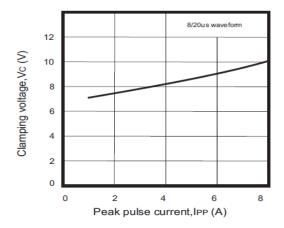


Fig 3: Clamping Voltage VS Peak Pulse Current

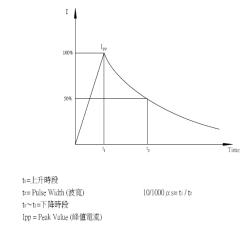


Fig 4: Forward Voltage Drop V.S Peak Forward Current





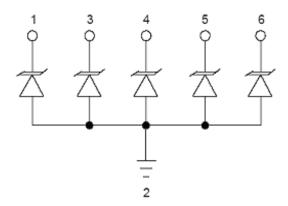
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APPLICATION NOTE

Device Connection for Protection of Five Data Lines

ESDV65V0U is designed to protect up to five data lines. The device is connected as follows:

- 1. The TVS protection of five I/O lines is achieved by connecting pins 1, 3, 4, 5, and 6 to the data lines.
- 2. Pin 2 is connected to ground.
- 3. The ground connection should be made directly to the ground plane for best results.
- 4. The path length is kept as short as possible to reduce the effects of parasitic inductance.

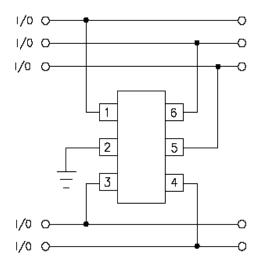


Circuit Board Layout Recommendations for Suppression of ESD

Good circuit board layout is critical for the suppression of ESD induced transients.

The following guidelines are recommended:

- 1. Place the TVS near the input terminals or connectors to restrict transient coupling.
- 2. Minimize the path length between the TVS and the protected line.
- 3. Minimize all conductive loops including power and ground loops.
- 4. The ESD transient return path to ground should be kept as short as possible.
- 5. Never run critical signals near board edges.
- 6. Use ground planes whenever possible.



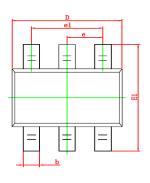
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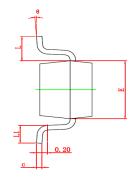


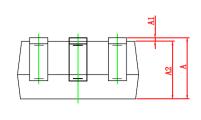
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SOT-363 PACKAGE OUTLINE







Symbol -	Dimensions in Millimeter		Dimensions in Inch	
	Min	Max	Min	Max
А	0.90	1.10	0.035	0.043
A1	0.00	0.10	0.000	0.004
A2	0.90	1.00	0.035	0.039
b	0.15	0.35	0.006	0.014
С	0.08	0.15	0.003	0.006
D	2.00	2.20	0.079	0.087
E	1.15	1.35	0.045	0.063
E1	2.15	2.45	0.085	0.096
е	0.65 TYP		0.026 TYP	
e1	1.20	1.40	0.047	0.055
L	0.525 TYP		0.021 TYP	
L1	0.26	0.46	0.010	0.018
θ	00	80	00	8°